

MITSUBISHI IGBT MODULES

CM100RL-12NF

HIGH POWER SWITCHING USE

CM100RL-12NF



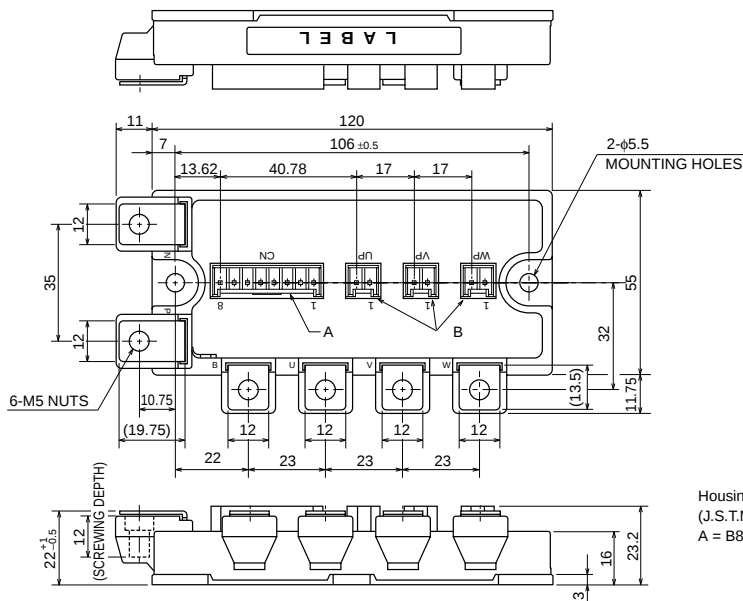
- IC 100A
- VCES 600V
- Insulated Type
- 7-elements in a pack

APPLICATION

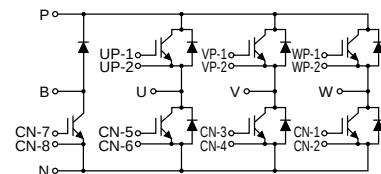
AC drive inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Housing Type of A and B
(J.S.T.Mfg.Co.Ltd)
A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

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ABSOLUTE MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	± 20	V
I _C	Collector current	DC, $T_c = 99^\circ\text{C}^{*1}$	100	A
I _{CM}		Pulse (Note 2)	200	A
I _E (Note 1)	Emitter current		100	A
I _{EM} (Note 1)		Pulse (Note 2)	200	A
P _C (Note 3)	Maximum collector dissipation	$T_c = 25^\circ\text{C}$	540	W

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V _{CES}	Collector-emitter voltage	G-E Short	600	V
V _{GES}	Gate-emitter voltage	C-E Short	± 20	V
I _C	Collector current	DC, $T_c = 107^\circ\text{C}^{*1}$	50	A
I _{CM}		Pulse (Note 2)	100	A
P _C (Note 3)	Maximum collector dissipation	$T_c = 25^\circ\text{C}$	320	W
V _{RRM}	Repetitive peak reverse voltage	Clamp diode part	600	V
I _{FM}	Forward current	Clamp diode part	50	A

(COMMON RATING)

Symbol	Parameter	Conditions	Ratings	Unit
T _j	Junction temperature		-40 ~ +150	$^\circ\text{C}$
T _{stg}	Storage temperature		-40 ~ +125	$^\circ\text{C}$
V _{iso}	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M5	2.5 ~ 3.5	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	350	g

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ELECTRICAL CHARACTERISTICS (T_j = 25°C)

INVERTER PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 10mA, VCE = 10V	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 100A, VGE = 15V	—	1.7	2.2	V
		T _j = 25°C	—	1.7	—	
		T _j = 125°C	—	—	—	
Cies	Input capacitance	VCE = 10V	—	—	15	nF
Coes	Output capacitance	VGE = 0V	—	—	1.9	nF
Cres	Reverse transfer capacitance		—	—	0.6	nF
QG	Total gate charge	VCC = 300V, IC = 100A, VGE = 15V	—	400	—	nC
td(on)	Turn-on delay time		—	—	120	ns
tr	Turn-on rise time	VCC = 300V, IC = 100A	—	—	100	ns
td(off)	Turn-off delay time	VGE1 = VGE2 = 15V	—	—	300	ns
tr	Turn-off fall time	RG = 6.3Ω, Inductive load switching operation	—	—	300	ns
trr (Note 1)	Reverse recovery time	IE = 100A	—	—	120	ns
Qrr (Note 1)	Reverse recovery charge		—	2.1	—	μC
VEC(Note 1)	Emitter-collector voltage	IE = 100A, VGE = 0V	—	—	2.8	V
Rth(j-c)Q	Thermal resistance	IGBT part (1/6 module)*1	—	—	0.23	°C/W
Rth(j-c)R		FWDi part (1/6 module)*1	—	—	0.41	°C/W
Rth(c-f)	Contact thermal resistance	Case to fin, Thermal compound Applied (1/6 module)*2	—	0.085	—	°C/W
RG	External gate resistance		6.3	—	63	Ω

BRAKE PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 5.0mA	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 50A, VGE = 15V	—	1.7	2.2	V
		T _j = 25°C	—	1.7	—	
		T _j = 125°C	—	—	—	
Cies	Input capacitance	VCE = 10V	—	—	7.5	nF
Coes	Output capacitance	VGE = 0V	—	—	1.0	nF
Cres	Reverse transfer capacitance		—	—	0.3	nF
QG	Total gate charge	VCC = 300V, IC = 50A, VGE = 15V	—	200	—	nC
VFM	Forward voltage drop	IF = 50A	—	—	2.8	V
Rth(j-c)Q	Thermal resistance	IGBT part*1	—	—	0.39	°C/W
Rth(j-c)R		Clamp diode part*1	—	—	0.70	°C/W
RG	External gate resistance		13	—	130	Ω

*1 : T_c measured point is just under the chips.

If you use this value, Rth(j-a) should be measured just under the chips.

*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

Note 1. IE, VEC, trr & Qrr represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

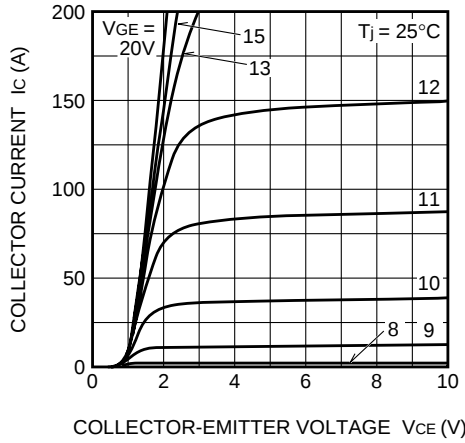
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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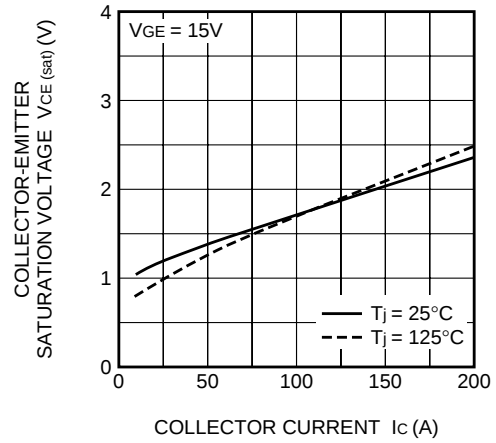
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

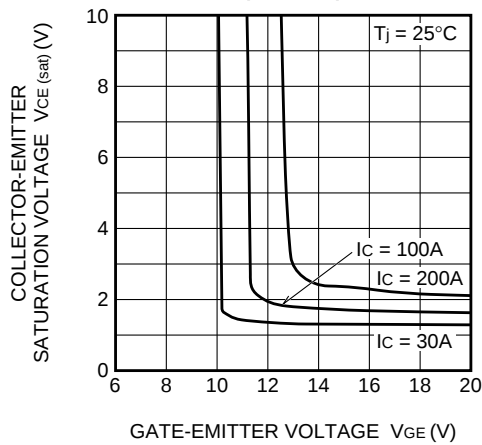
OUTPUT CHARACTERISTICS
(TYPICAL)



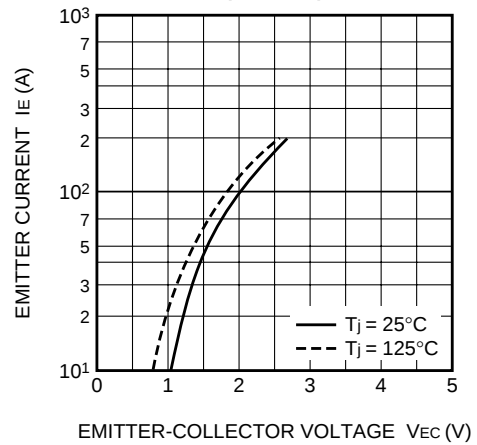
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



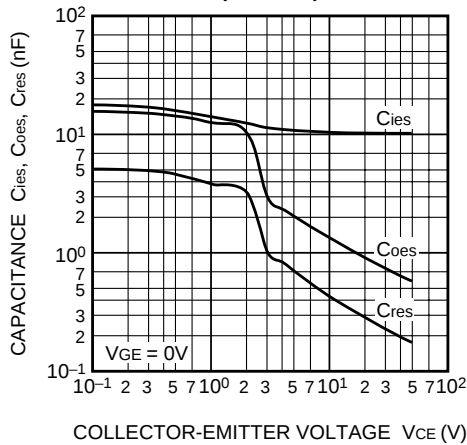
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



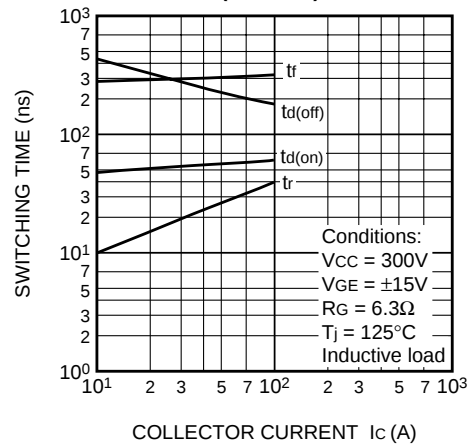
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CAPACITANCE- V_{CE}
CHARACTERISTICS
(TYPICAL)



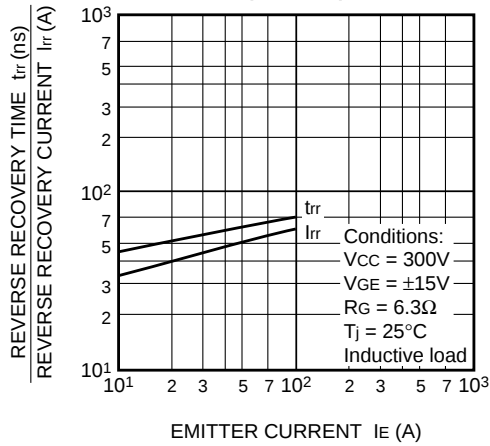
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



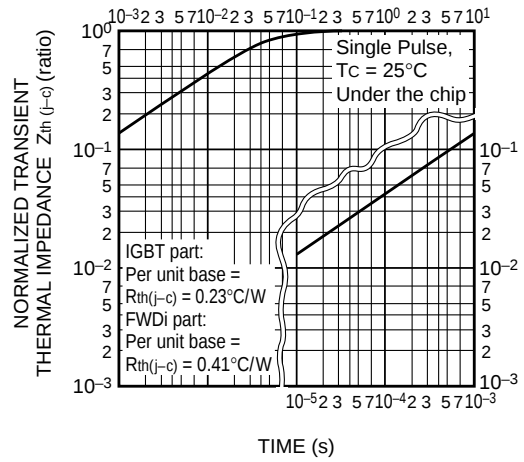
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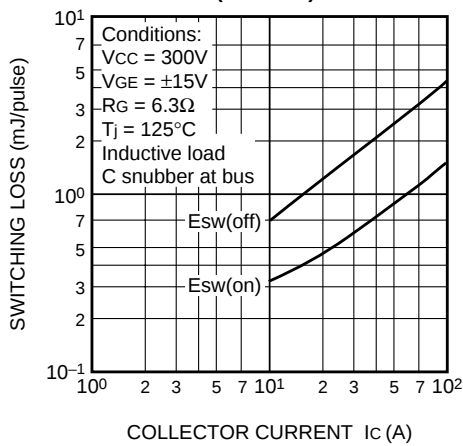
REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



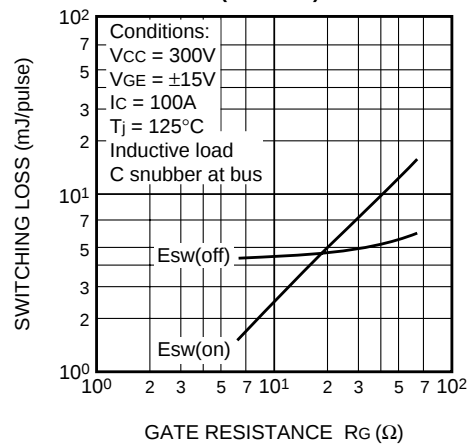
TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part & FWDi part)



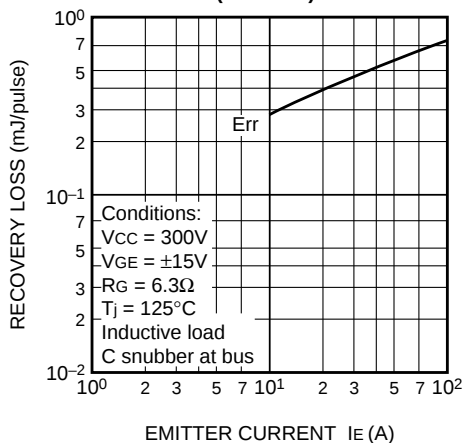
SWITCHING LOSS vs.
COLLECTOR CURRENT
(TYPICAL)



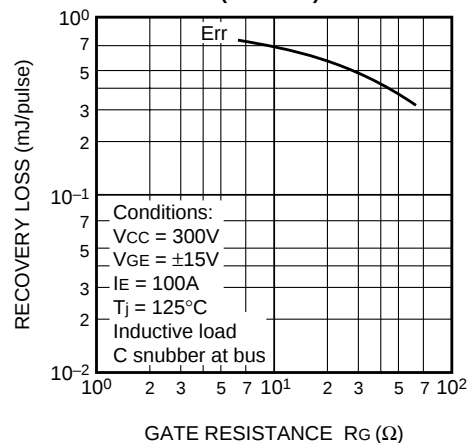
SWITCHING LOSS vs.
GATE RESISTANCE
(TYPICAL)



RECOVERY LOSS vs. IE
(TYPICAL)



RECOVERY LOSS vs.
GATE RESISTANCE
(TYPICAL)



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